

20Amp. Schottky Barrier Rectifiers

MBR20150E3

| | |
|-------------|----------------|
| $I_{F(AV)}$ | $2 \times 10A$ |
| V_{RRM} | 150V |
| T_j | 175°C |
| V_F | 0.68V |

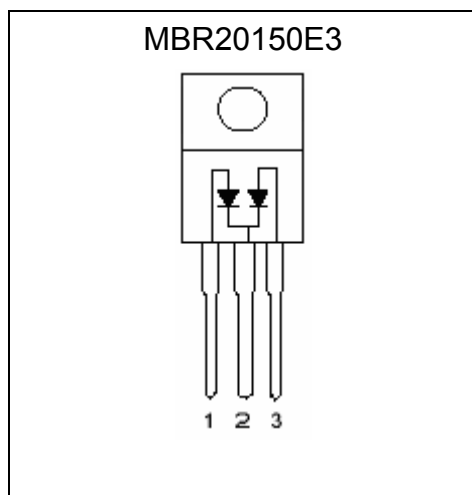
Features

- 175°C operating junction temperature
- Low V_F and low I_R type
- Metal silicon junction, major carrier conduction
- 20A total (10A per diode leg)
- Guardring for stress protection
- Low power loss, high efficiency
- High surge capability
- High temperature soldering guaranteed : 260°C/10s, 0.25”(6.35mm) from case
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection application
- RoHS compliant package

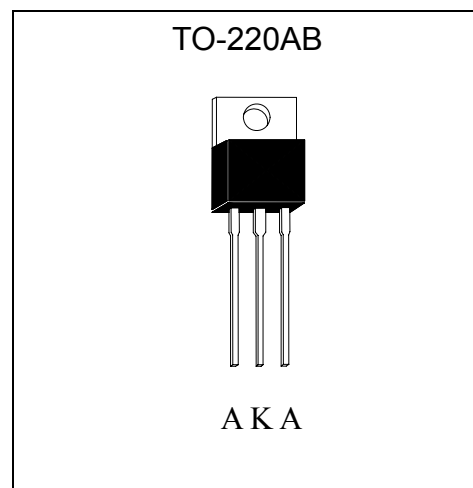
Mechanical Data

- Case: JEDEC TO-220AB molded plastic
- Mounting Position: Any
- Weight: 0.08 ounce, 2.24 grams
- Terminals: Pure tin plated, lead-free, solderable per MIL-STD-750 method 2026
- Epoxy: UL 94V-0 rate flame retardant
- Mounting Torque : 5 in-lbs max

Equivalent Circuit



Outline





Maximum Ratings and Electrical Characteristics (Per Diode Leg)

(Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

| Parameter | Symbol | Min. | Typ. | Max. | Units |
|---|--------------------|------|------|--------------------|-------|
| Maximum Recurrent peak reverse voltage | V _{RRM} | | | 150 | V |
| Maximum RMS voltage | V _{RMS} | | | 100 | V |
| Maximum DC blocking voltage | V _{DC} | | | 150 | V |
| Maximum instantaneous forward voltage at (Note 1) | V _F | | 0.68 | 0.85 | V |
| | | | | IF=10A, Tc=125°C | |
| | | | | IF=20 A, Tc=25°C | |
| | | | | IF=20A, Tc=125°C | |
| Maximum Average forward rectified current @ Tc=134°C | I _{F(AV)} | | | 10 | A |
| | | | | Per Diode | |
| Non-repetitive peak forward surge current @ 8.3ms single half sine wave superimposed on rated load (JEDEC method) | I _{FSM} | | | 150 | A |
| Peak repetitive reverse surge current, Tj<175°C (Note 1) | I _{RRM} | | | 3 | A |
| Maximum instantaneous reverse current at | I _R | | | 5 | μA |
| | | | | VR=150 V, Tc=125°C | 5 |
| Voltage rate of change, (rated V _R) | dV/dt | | | 10,000 | V/μs |
| Typical junction capacitance @ f=1MHz and applied 5V reverse voltage | C _J | | 168 | | pF |
| ESD susceptibility (Note 2) | | | | 8000 | V |
| Storage temperature range | T _{stg} | -65 | | +175 | °C |
| Operating junction temperature range | T _J | -65 | | +175 | °C |

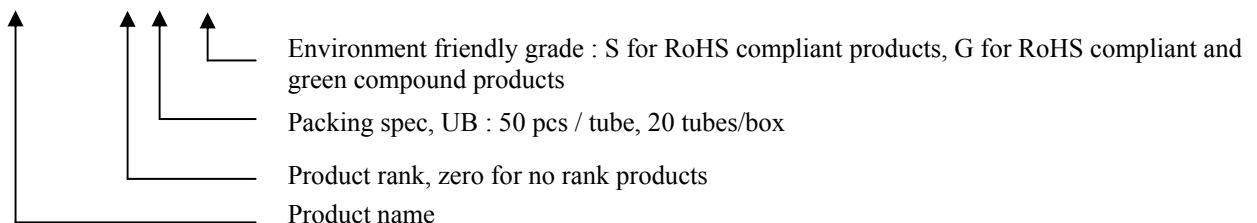
Notes : 1. 2.0μs pulse width, f=1.0kHz
 2. Human body model, 1.5kΩ in series with 100pF

Thermal Data

| Parameter | Symbol | Value | Unit |
|---|---------------------|-------|------|
| Maximum Thermal Resistance, Junction-to-case | R _{th,j-c} | 2.0 | °C/W |
| Maximum Thermal Resistance, Junction-to-ambient | R _{th,j-a} | 60 | °C/W |

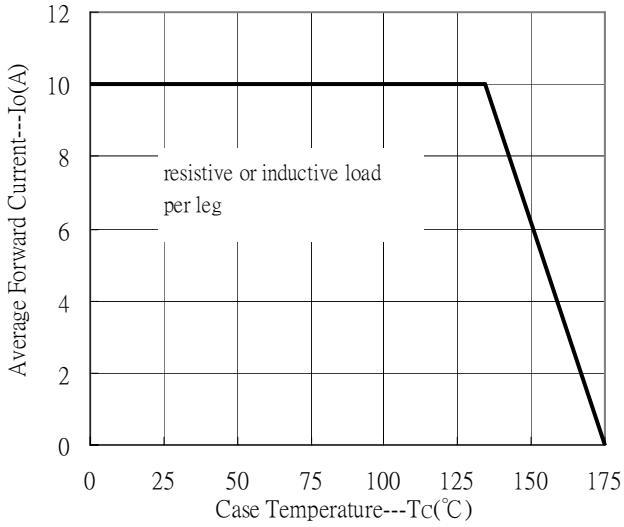
Ordering Information

| Device | Package | Shipping |
|-------------------|----------------------------------|---|
| MBR20150E3-0-UB-S | TO-220 (Pb-free lead plating) | 50 pcs / tube, 20 tubes/ box , 4 boxes/carton |

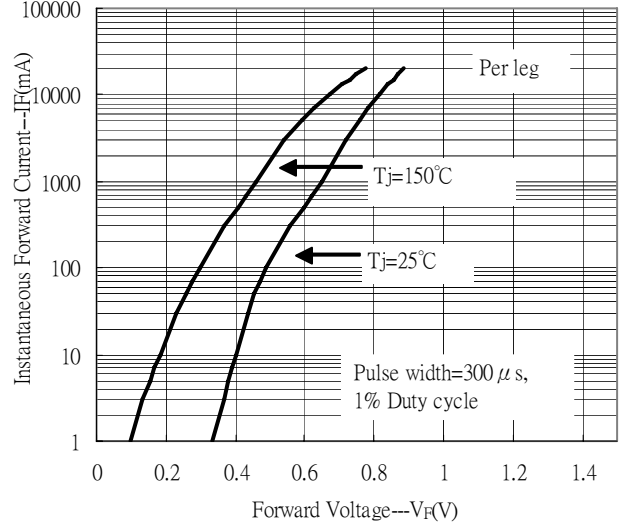


Characteristic Curves

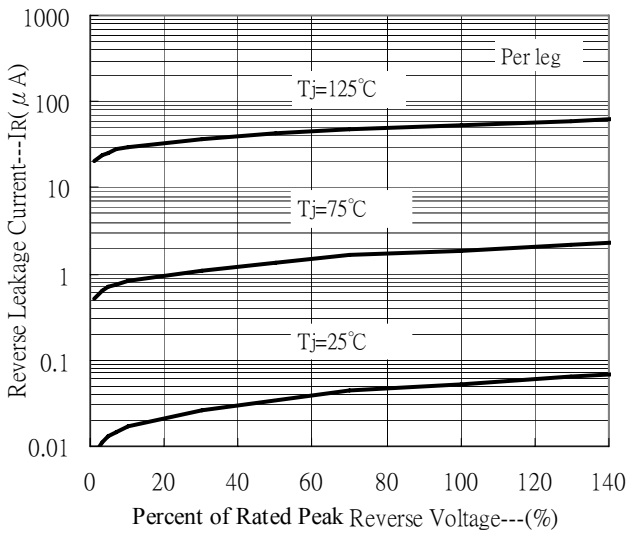
Forward Current Derating Curve



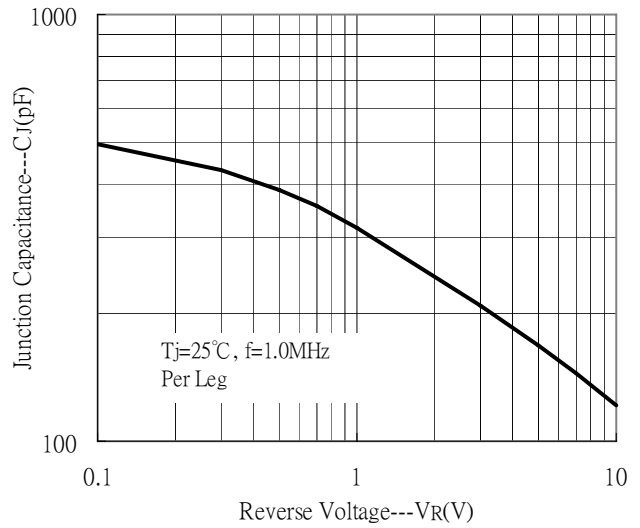
Forward Current vs Forward Voltage



Reverse Leakage Current vs Reverse Voltage



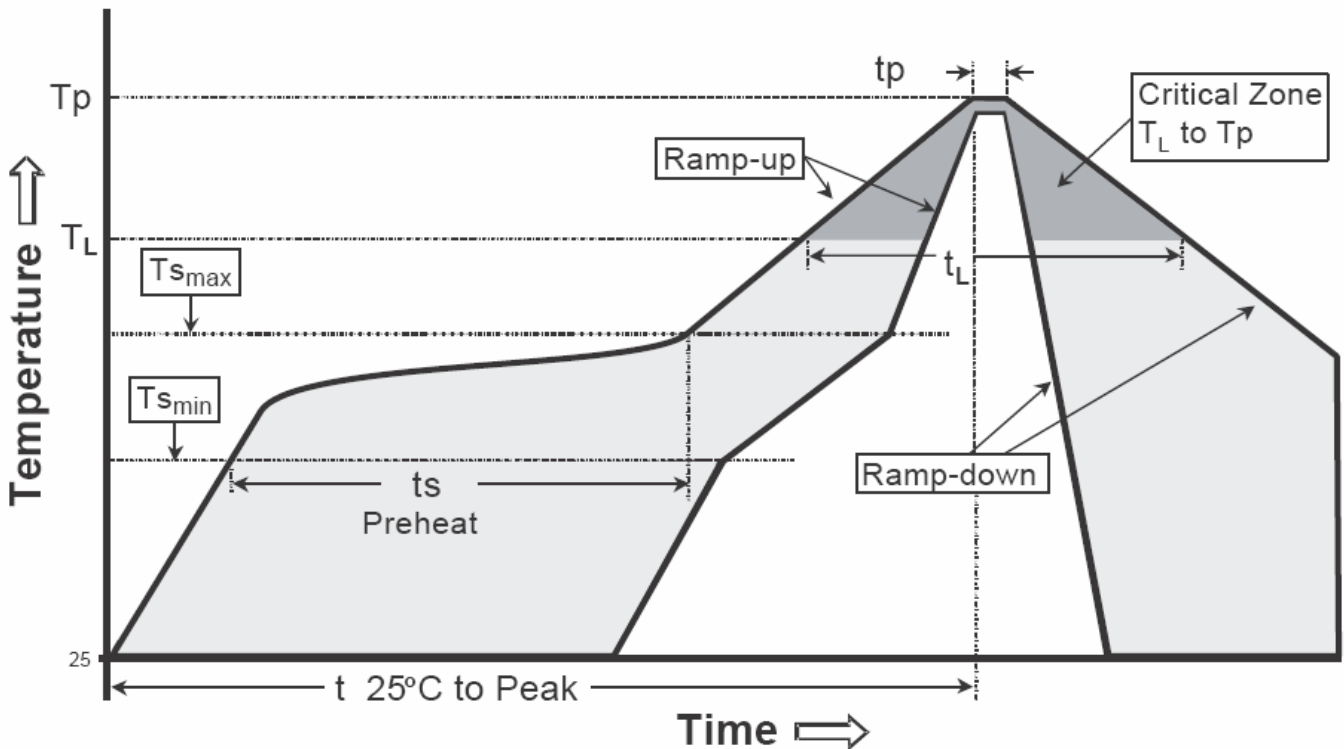
Junction Capacitance vs Reverse Voltage



Recommended wave soldering condition

| | | |
|-----------------|------------------|-----------------|
| Product | Peak Temperature | Soldering Time |
| Pb-free devices | 260 +0/-5 °C | 5 +1/-1 seconds |

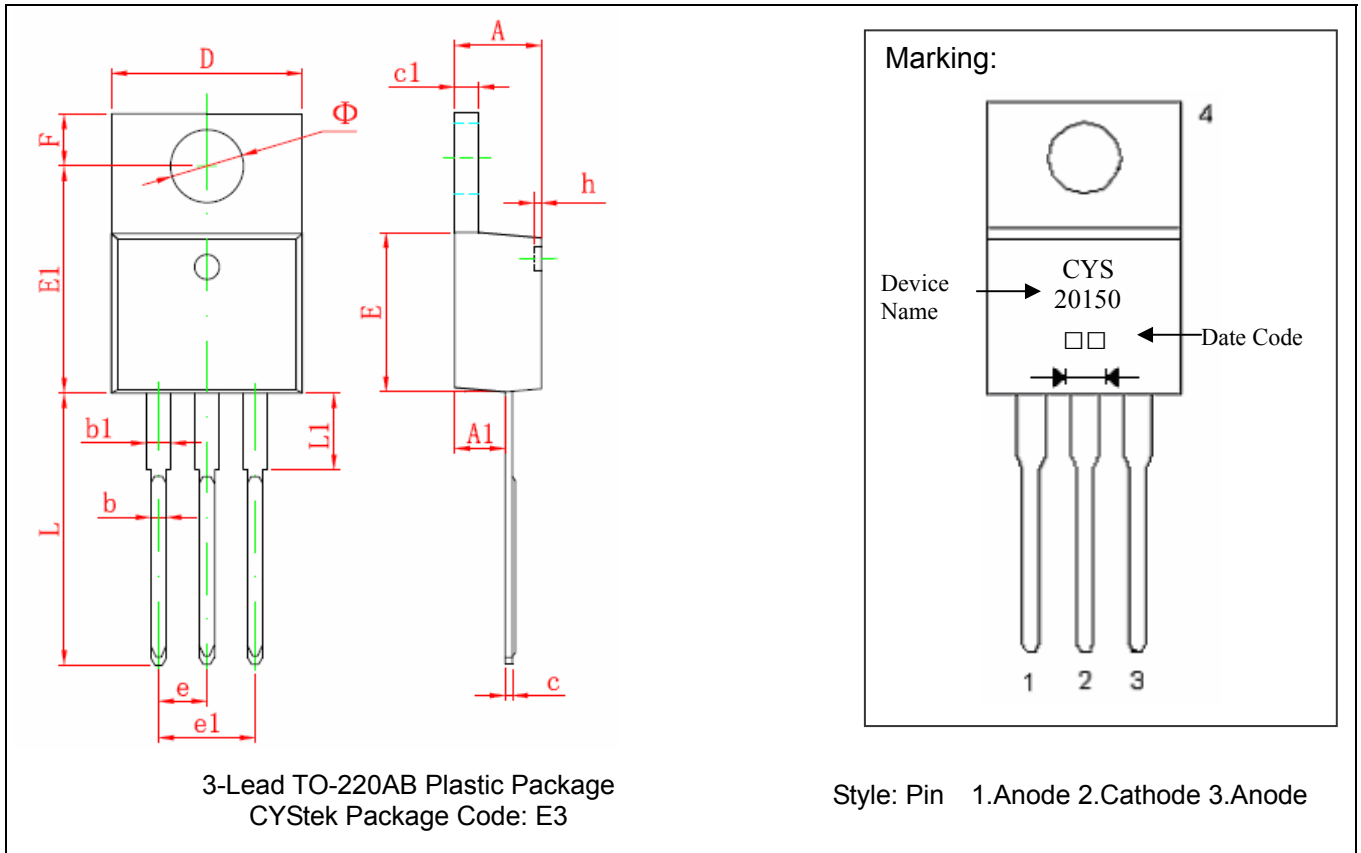
Recommended temperature profile for IR reflow



| Profile feature | Sn-Pb eutectic Assembly | Pb-free Assembly |
|--|-------------------------|------------------|
| Average ramp-up rate (Tsmax to Tp) | 3°C/second max. | 3°C/second max. |
| Preheat | | |
| -Temperature Min(Ts min) | 100°C | 150°C |
| -Temperature Max(Ts max) | 150°C | 200°C |
| -Time(ts min to ts max) | 60-120 seconds | 60-180 seconds |
| Time maintained above: | | |
| -Temperature (Tl) | 183°C | 217°C |
| - Time (tl) | 60-150 seconds | 60-150 seconds |
| Peak Temperature(Tp) | 240 +0/-5 °C | 260 +0/-5 °C |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds | 20-40 seconds |
| Ramp down rate | 6°C/second max. | 6°C/second max. |
| Time 25 °C to peak temperature | 6 minutes max. | 8 minutes max. |

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-220AB Dimension



3-Lead TO-220AB Plastic Package
 CYStek Package Code: E3

Style: Pin 1.Anode 2.Cathode 3.Anode

*: Typical

| DIM | Millimeters | | Inches | | DIM | Millimeters | | Inches | |
|-----|-------------|--------|--------|-------|-----|-------------|--------|--------|-------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 4.470 | 4.670 | 0.176 | 0.184 | E1 | 12.060 | 12.460 | 0.475 | 0.491 |
| A1 | 2.520 | 2.820 | 0.099 | 0.111 | e | 2.540* | | 0.100* | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | e1 | 4.980 | 5.180 | 0.196 | 0.204 |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | F | 2.590 | 2.890 | 0.102 | 0.114 |
| c | 0.310 | 0.530 | 0.012 | 0.021 | h | 0.000 | 0.300 | 0.000 | 0.012 |
| c1 | 1.170 | 1.370 | 0.046 | 0.054 | L | 13.400 | 13.800 | 0.528 | 0.543 |
| D | 10.010 | 10.310 | 0.394 | 0.406 | L1 | 3.560 | 3.960 | 0.140 | 0.156 |
| E | 8.500 | 8.900 | 0.335 | 0.350 | Φ | 3.735 | 3.935 | 0.147 | 0.155 |

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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